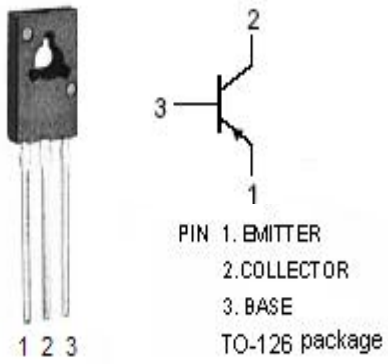
isc Silicon PNP Power Transistor — BD132

ESCRIPTION

- DC Current Gain-
  : h_{FE}= 40(Min)@ I_C= -0.5A
- Collector-Emitter Breakdown Voltage -
  : $V_{(BR)CEO}$= -45V(Min.)
- Complement to type BD131
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

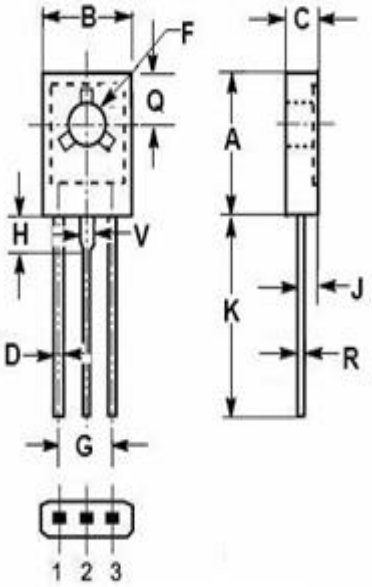
- Designed for medium power and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-6	A
I_{BM}	Base Current-Peak	-0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	6	℃/W



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-0.7	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0 V_{CB}= -40V; I_E= 0,T_C=150℃			-50 -10	nA μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C= 0			-50	nA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -12V	40			
h_{FE-2}	DC Current Gain	I_C= -2A; V_{CE}= -1V	20			
f_T	Current-Gain—Bandwidth Product	I_C= -0.25A; V_{CE}= -5V	60			MHz